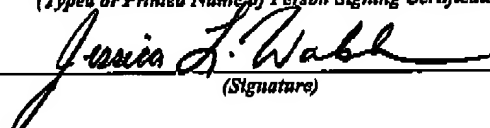


<b>CERTIFICATE OF TRANSMISSION BY FACSIMILE (37 CFR 1.8)</b> Applicant(s): <b>S. SUNDAR KUMAR IYER ET AL.</b>			<b>Docket No.</b> <b>FIS920000372US1</b>
<b>Serial No.</b> <b>09/878,556</b>	<b>Filing Date</b> <b>06/11/2001</b>	<b>Examiner</b> <b>J. CHEN</b>	<b>Group Art Unit</b> <b>2813</b>
<b>Invention: METHOD FOR FORMING VARIABLE OXIDE THICKNESS ACROSS SEMICONDUCTOR CHIPS</b>			
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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	S. SUNDAR KUMAR IYER, ET AL.	)	
		)	Group Art Unit: 2813
Serial No.:	09/878,556	)	
		)	
Filed:	June 11, 2001	)	Examiner: Chen, J.
		)	
For:	METHOD OF FORMING VARIABLE	)	
	OXIDE THICKNESS ACROSS	)	Confirmation No.: 3210
	SEMICONDUCTOR CHIPS	)	

**RESPONSE TO OFFICE ACTION**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

In response to the Office Action mailed January 12, 2004, the Applicants submit the following remarks: